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## NTE2691 (NPN) & NTE2692 (PNP) Silicon Complementary Transistors High Voltage Switch

### **Features:**

- High Breakdown Voltage
- Large Current Capacity

### **Absolute Maximum Ratings:** ( $T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector–Base Voltage, $V_{CBO}$ .....	180V
Collector–Emitter Voltage, $V_{CEO}$ .....	160V
Emitter–Base Voltage, $V_{EBO}$ .....	6V
Collector Current, $I_C$	
Continuous .....	1.5A
Pulse .....	2.5A
Collector Dissipation, $P_C$ .....	1W
Maximum Junction Temperature, $T_J$ .....	+150°C
Storage Temperature Range, $T_{stg}$ .....	−55° to +150°C

### **Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 120\text{V}$ , $I_E = 0$	—	—	1	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 4\text{V}$ , $I_C = 0$	—	—	1	$\mu\text{A}$
DC Current Gain NTE2691	$h_{FE1}$	$V_{CE} = 5\text{V}$ , $I_C = 100\text{mA}$	140	—	280	
NTE2692			200	—	400	
DC Current Gain	$h_{FE2}$	$V_{CE} = 5\text{V}$ , $I_C = 10\text{mA}$	80	—	—	
Gain–Bandwidth Product	$f_T$	$V_{CE} = 10\text{V}$ , $I_C = 50\text{mA}$	—	120	—	MHz
Output Capacitance NTE2691	$C_{ob}$	$V_{CB} = 10\text{V}$ , $f = 1\text{MHz}$	—	14	—	pF
NTE2692			—	22	—	pF
Collector–Emitter Saturation Voltage NTE2691	$V_{CE(sat)}$	$I_C = 500\text{mA}$ , $I_B = 50\text{mA}$	—	130	450	mV
NTE2692			—	200	500	mV
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 500\text{mA}$ , $I_B = 50\text{mA}$	—	0.85	1.2	V



**Electrical Characteristics (Cont'd):** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$V_{(\text{BR})\text{CBO}}$	$I_C = 10\mu\text{A}, I_E = 0$	180	—	—	V
Collector-Emitter Breakdown Voltage	$V_{(\text{BR})\text{CEO}}$	$I_C = 1\text{mA}, R_{BE} = \infty$	160	—	—	V
Emitter-Base Breakdown Voltage	$V_{(\text{BR})\text{EBO}}$	$I_E = 10\mu\text{A}, I_C = 0$	6	—	—	V
Turn-On Time	$t_{\text{on}}$	$I_C = 10I_{B1} = -10I_{B1} = 700\text{mA}, V_{CC} = 100\text{V}, \text{Pulse Width} = 20\mu\text{s}, \text{Duty Cycle} \leq 1\%$	—	40	—	$\mu\text{s}$
Storage Time NTE2691	$t_{\text{stg}}$		—	1.2	—	$\mu\text{s}$
NTE2692			—	0.7	—	$\mu\text{s}$
Fall Time NTE2691	$t_f$		—	80	—	ns
NTE2692			—	40	—	ns

